

MBRM110LT1G, NRVBM110LT1G, NRVBM110LT3G

Surface Mount Schottky Power Rectifier

POWERMITE®

Power Surface Mount Package

The Schottky POWERMITE® employs the Schottky Barrier principle with a barrier metal and epitaxial construction that produces optimal forward voltage drop–reverse current tradeoff. The advanced packaging techniques provide for a highly efficient micro miniature, space saving surface mount Rectifier. With its unique heatsink design, the POWERMITE® has the same thermal performance as the SMA while being 50% smaller in footprint area, and delivering one of the lowest height profiles, < 1.1 mm in the industry. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC–DC and DC–DC converters, reverse battery protection, and “ORing” of multiple supply voltages and any other application where performance and size are critical.

Features

- Ultra Low V_F
- 1st in Marketplace with a 10 V_R Schottky Rectifier
- Low Profile – Maximum Height of 1.1 mm
- Small Footprint – Footprint Area of 8.45 mm²
- Low Thermal Resistance with Direct Thermal Path of Die on Exposed Cathode Heat Sink
- ESD Ratings:
 - ♦ Human Body Model > 4000 V (Class 3)
 - ♦ Machine Model > 400 V (Class C)
- AEC–Q101 Qualified and PPAP Capable
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- All Packages are Pb–Free*

Mechanical Characteristics:

- POWERMITE® is JEDEC Registered as D0–216AA
- Case: Molded Epoxy
- Epoxy Meets UL 94 V–0 @ 0.125 in
- Weight: 62 mg (Approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Maximum for 10 Seconds

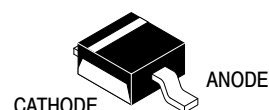
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

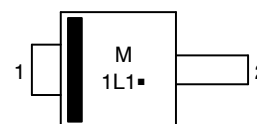
<http://onsemi.com>

SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES, 10 VOLTS



**POWERMITE
CASE 457
PLASTIC**

MARKING DIAGRAM



M = Date Code
1L1 = Device Code
■ = Pb–Free Package

ORDERING INFORMATION

Device	Package	Shipping†
MBRM110LT1G	POWERMITE (Pb–Free)	3,000 / Tape & Reel
NRVBM110LT1G	POWERMITE (Pb–Free)	3,000 / Tape & Reel
MBRM110LT3G	POWERMITE (Pb–Free)	12,000 / Tape & Reel
NRVBM110LT3G	POWERMITE (Pb–Free)	12,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	10	V
Average Rectified Forward Current ($T_L = 115^\circ\text{C}$, $R_{\theta JL} = 35^\circ\text{C/W}$)	I_O	1.0	A
Non-Repetitive Peak Surge Current (Non-Repetitive peak surge current, halfwave, single phase, 60 Hz)	I_{FSM}	50	A
Storage Temperature	T_{stg}	-55 to 125	$^\circ\text{C}$
Operating Junction Temperature	T_J	-55 to 125	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R , $T_J = 25^\circ\text{C}$)	dv/dt	10,000	$\text{V}/\mu\text{s}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead (Anode) (Note 1)	R_{tjl}	35	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Tab (Cathode) (Note 1)	R_{tjtab}	23	
Thermal Resistance, Junction-to-Ambient (Note 1)	R_{tja}	277	

1. Mounted with minimum recommended pad size, PC Board FR4, See Figures 8 and 9.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value		Unit
Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 0.1 \text{ A}$) ($I_F = 1.0 \text{ A}$) ($I_F = 2.0 \text{ A}$)	V_F	$T_J = 25^\circ\text{C}$	$T_J = 100^\circ\text{C}$	V
		0.280	0.175	
		0.365	0.275	
		0.415	0.325	
Maximum Instantaneous Reverse Current (Note 2) ($V_R = 5.0 \text{ V}$) ($V_R = 10 \text{ V}$)	I_R	$T_J = 25^\circ\text{C}$	$T_J = 100^\circ\text{C}$	mA
		0.2	30	
		0.5	60	

2. Pulse Test: Pulse Width $\leq 250 \mu\text{s}$, Duty Cycle $\leq 2\%$.

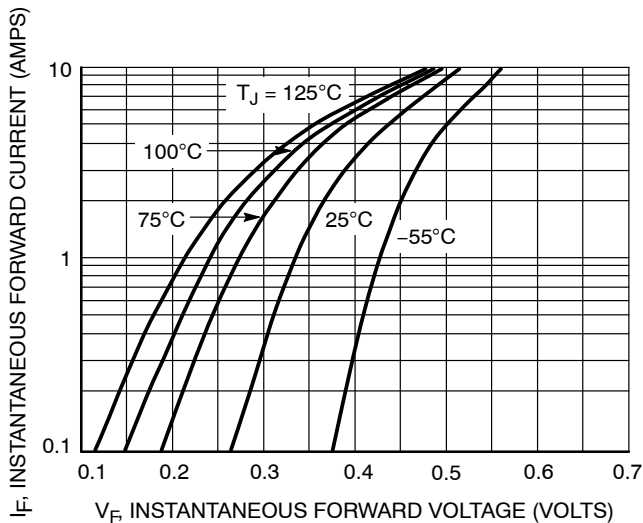


Figure 1. Typical Forward Voltage

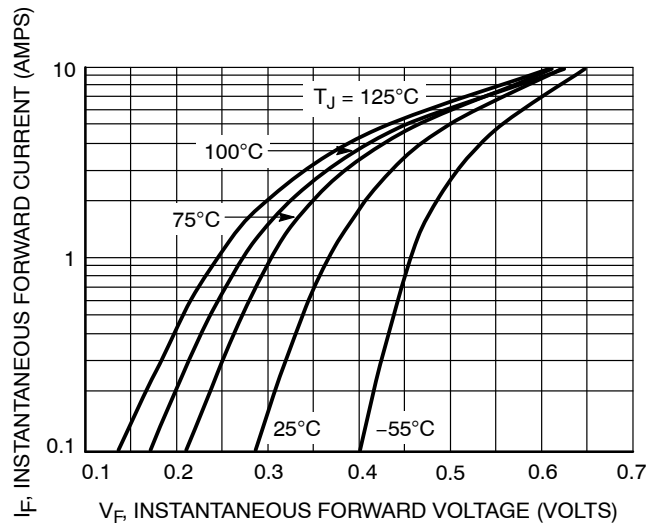


Figure 2. Maximum Forward Voltage

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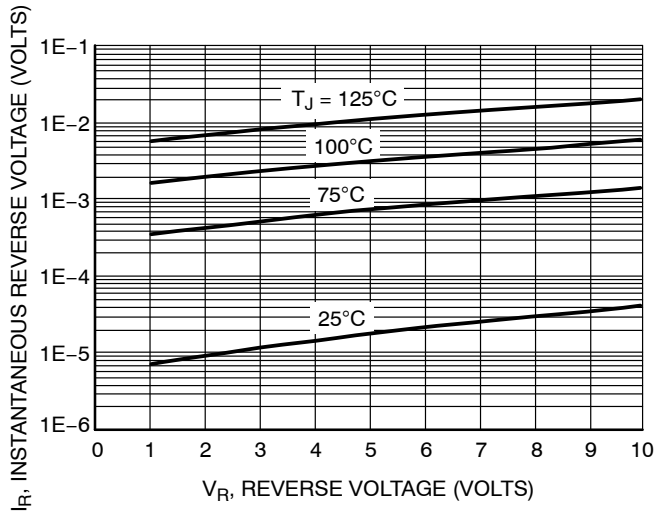


Figure 3. Typical Reverse Current

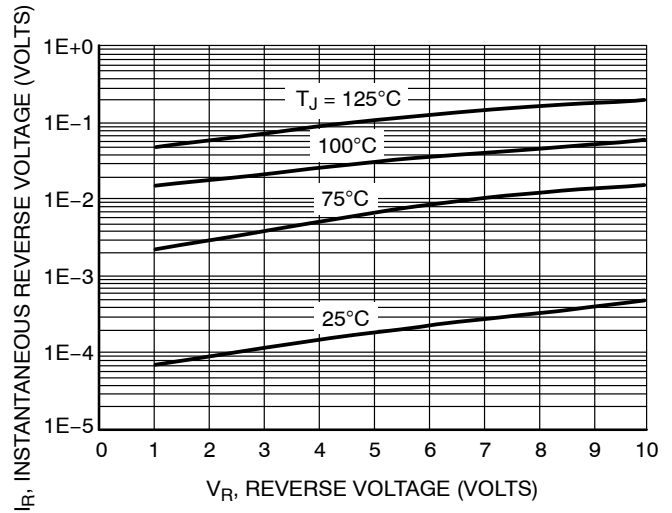


Figure 4. Maximum Reverse Current

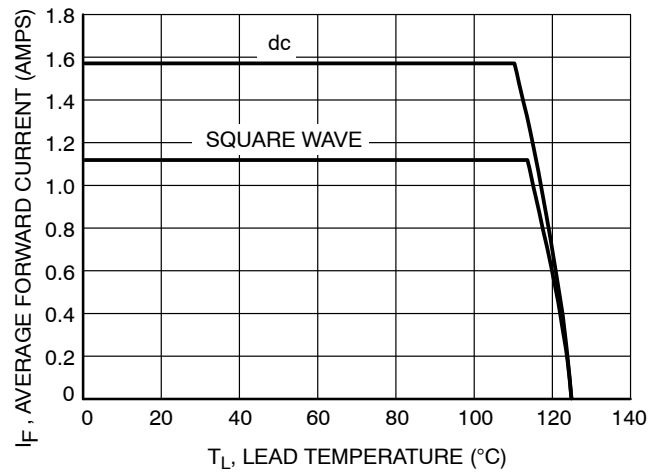


Figure 5. Current Derating – Junction to Lead

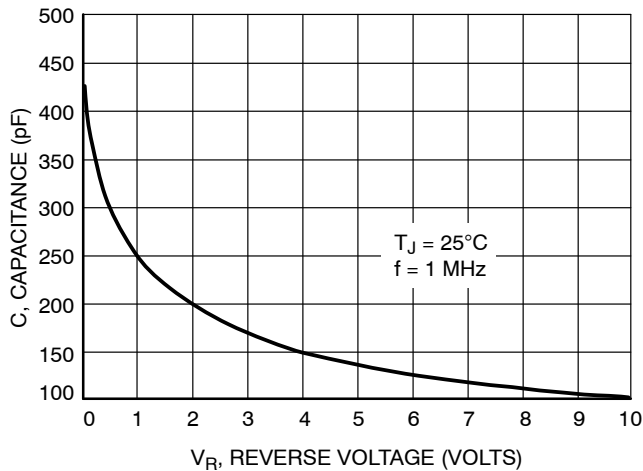


Figure 6. Typical Capacitance

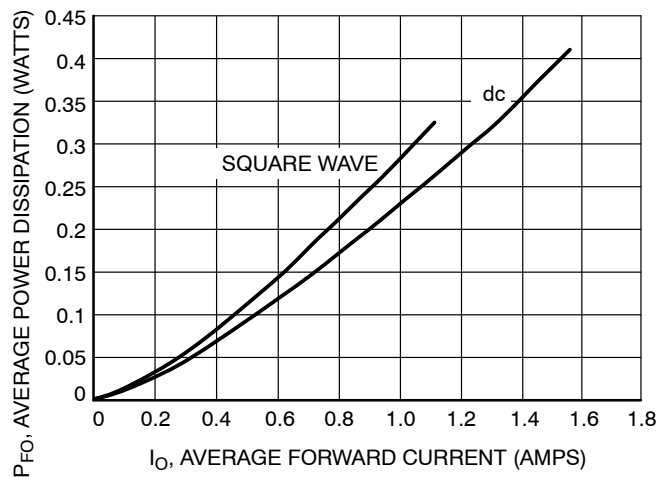


Figure 7. Forward Power Dissipation

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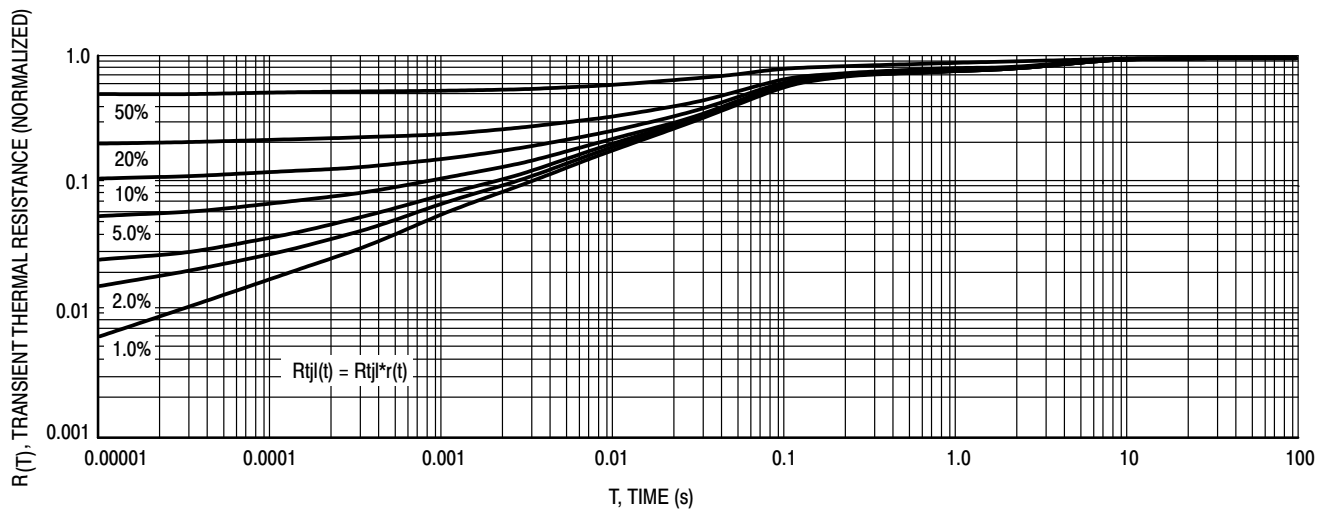


Figure 8. Thermal Response Junction to Lead

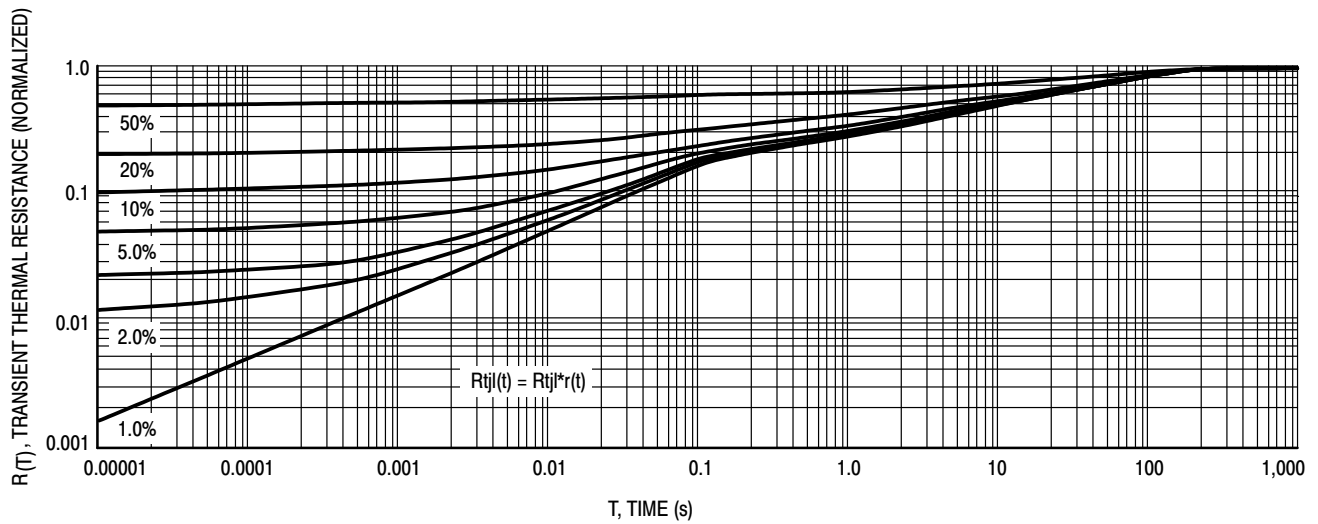
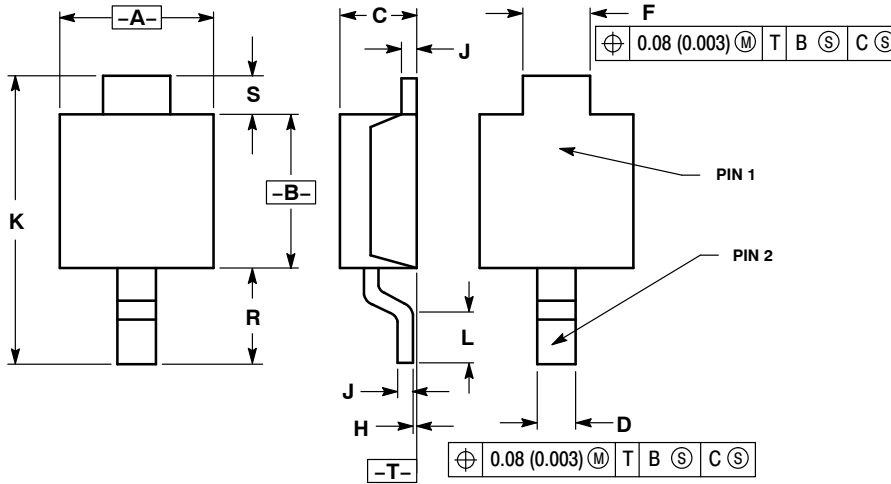


Figure 9. Thermal Response Junction to Ambient

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PACKAGE DIMENSIONS

POWERMITE
CASE 457-04
ISSUE E



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.75	2.05	0.069	0.081
B	1.75	2.18	0.069	0.086
C	0.85	1.15	0.033	0.045
D	0.40	0.69	0.016	0.027
F	0.70	1.00	0.028	0.039
H	-0.05	+0.10	-0.002	+0.004
J	0.10	0.25	0.004	0.010
K	3.60	3.90	0.142	0.154
L	0.50	0.80	0.020	0.031
R	1.20	1.50	0.047	0.059
S	0.50	REF	0.019	REF

STYLE 1:

1. CATHODE
2. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MBRM110L/D

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9